

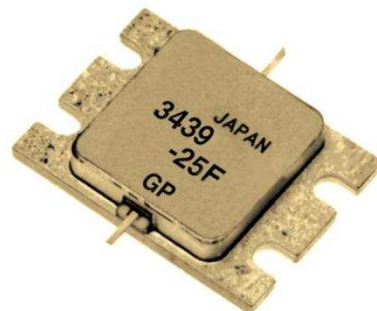
FEATURES

- High Output Power: $P_{1dB} = 44.5\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 10.5\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 41\%$ (Typ.)
- Low IM3 = $-46\text{dBc}@P_o = 33.5\text{dBm}$
- Broad Band: 3.4 to 3.9GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\text{ohm}$
- Hermetically Sealed Package

DESCRIPTION

The FLM3439-25F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

SEDI's stringent Quality Assurance Program assures the highest reliability and consistent performance.



ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25\text{deg.C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_c = 25\text{deg.C}$	93.7	W
Storage Temperature	T_{stg}		-65 to +175	deg.C
Channel Temperature	T_{ch}		175	deg.C

SEDI recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 64.0 and -11.2 mA respectively with gate resistance of 25ohm.

ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25\text{deg.C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS}=5V, V_{GS}=0V$	-	11.6	17.4	A
Transconductance	g_m	$V_{DS}=5V, I_{DS}=6.8A$	-	5800	-	mS
Pinch-off Voltage	V_p	$V_{DS}=5V, I_{DS}=600mA$	-1.0	-2.0	-3.5	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS}=-600\mu A$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS}=10V,$	43.5	44.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}	$I_{DS}=0.55 I_{DSS}$ (Typ.),	9.5	10.5	-	dB
Drain Current	I_{dsr}	$f=3.4 \text{ to } 3.9 \text{ GHz},$	-	6200	7600	mA
Power-added Efficiency	η_{add}	$Z_S=Z_L=50\text{ohm}$	-	41	-	%
Gain Flatness	ΔG		-	-	+/-0.6	dB
3rd Order Intermodulation Distortion	IM_3	$f = 3.9 \text{ GHz}, \Delta f = 10 \text{ MHz}$ 2-Tone Test $P_{out} = 33.5\text{dBm S.C.L.}$	-44	-46	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	1.4	1.6	deg.C/W
Channel Temperature Rise	ΔT_{ch}	$10V \times I_{dsr} \times R_{th}$	-	-	100	deg.C

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

CASE STYLE

IK

ESD

Class 3A

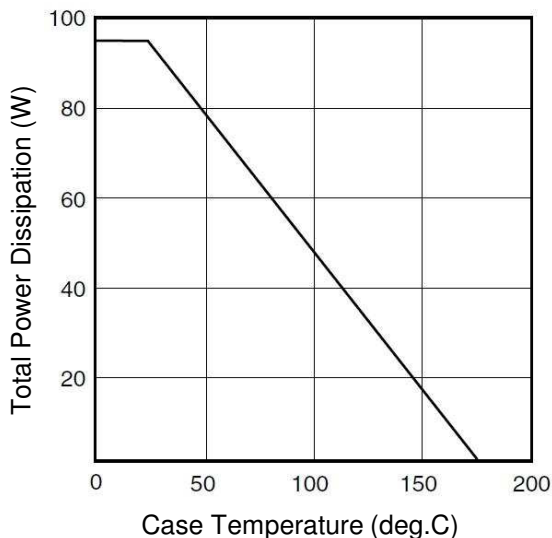
4000V to 8000V

Note : Based on EIAJ ED-4701 C-111A (C=100pF, R=1.5kohm)

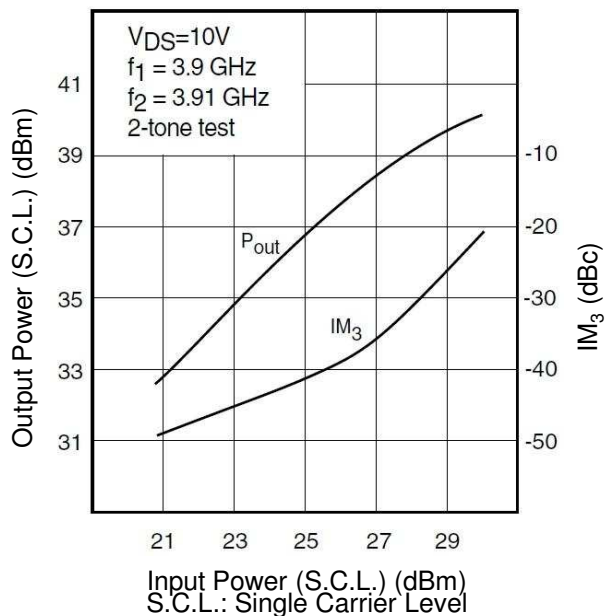
RoHS Compliance

Yes

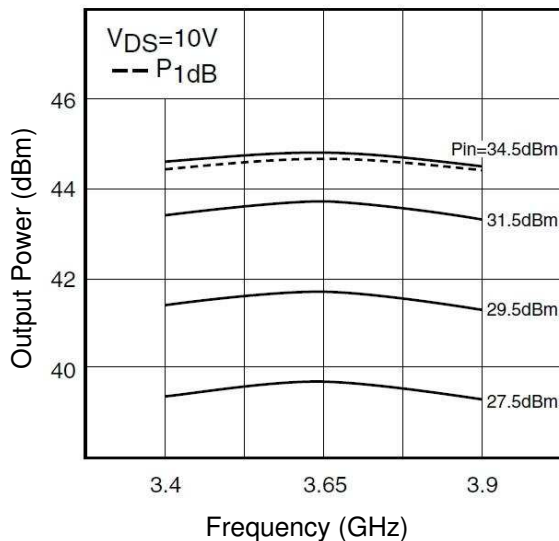
POWER DERATING CURVE



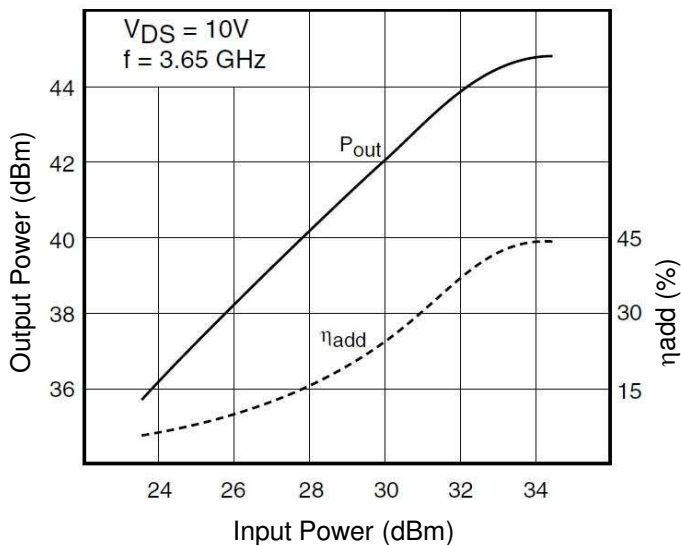
OUTPUT POWER & IM_3 vs. INPUT POWER

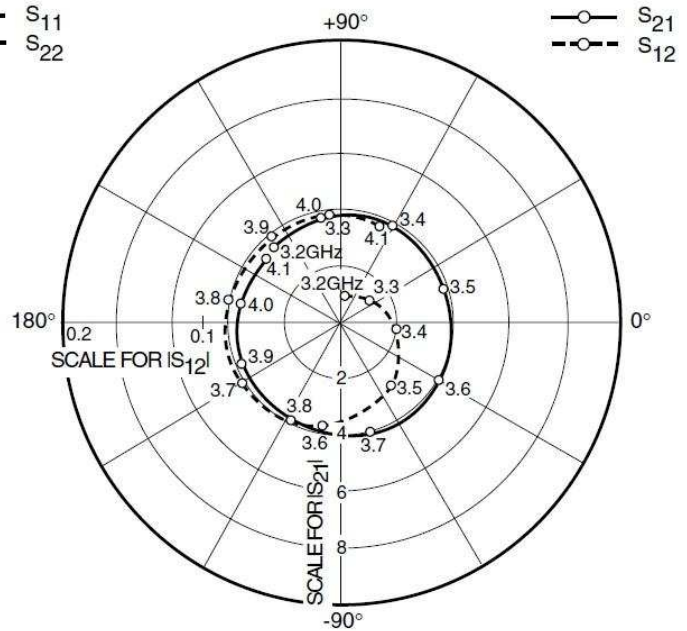
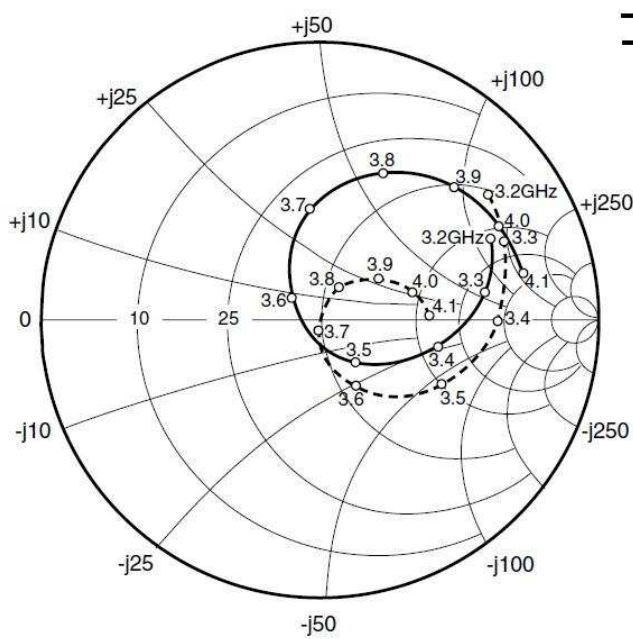


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER



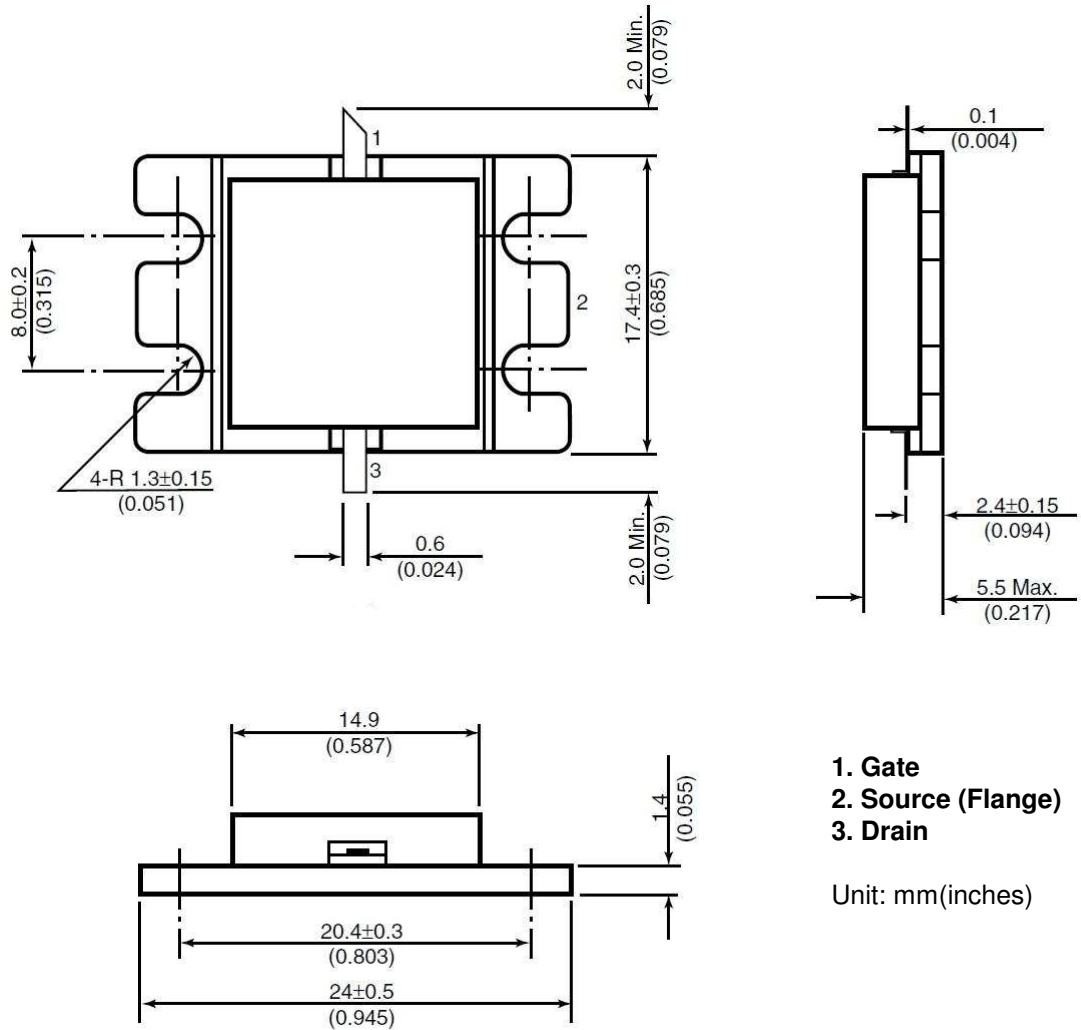


S-PARAMETERS

V_{DS} = 10V, I_{DS} = 6800mA

FREQUENCY (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
3200	0.675	25.7	3.631	132.1	0.018	81.3	0.753	37.0
3300	0.591	9.8	3.802	101.4	0.025	38.7	0.709	22.3
3400	0.440	-14.5	3.936	61.7	0.039	-6.7	0.631	-0.5
3500	0.198	-50.0	3.799	17.8	0.058	-52.4	0.493	-28.9
3600	0.130	139.2	4.074	-29.2	0.075	-101.5	0.273	-62.6
3700	0.403	95.0	4.027	-76.3	0.083	-148.7	0.046	-105.4
3800	0.582	67.2	3.981	-118.4	0.083	169.3	0.134	62.2
3900	0.679	45.1	3.890	-157.6	0.079	130.4	0.262	36.4
4000	0.721	27.6	3.631	168.3	0.076	96.9	0.343	16.2
4100	0.739	13.4	3.508	139.8	0.073	68.8	0.397	1.2

Case Style "IK" Metal-Ceramic Hermetic Package



For further information please contact:

<http://global-sei.com/Electro-optic/about/office.html>

CAUTION

This product contains **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.